

Please amend claims 27, 29, 35, and 41 as follows:

Sub C 10
27. (Twice Amended) A method of etching oxide using a polymer, the method comprising:

disposing a patterned semiconductor substrate in a high density plasma etcher, said substrate comprising a silicon layer with a gate stack structure disposed thereon, said gate stack structure being encapsulated by silicon nitride, and layered with an oxide;

b1
providing a hydrofluorcarbon gas into said high density etcher;

selectively removing portions of said oxide by pulsing a fluorocarbon gas; wherein:

 said pulsing imparts a time varying flow rate to said fluorocarbon gas for a plurality of periods of said time varying flow rate; and

 said fluorocarbon gas forms a protective layer; and

wherein the pulsing of said fluorocarbon gas causes said hydrofluorcarbon gas to have cyclical concentrations within said high density etcher.

Sub C 11
29. (Twice Amended) The method as defined in Claim 27, wherein said hydrofluorcarbon gas is pulsed into said high density etcher so that the hydrofluorcarbon gas pulses alternate with the fluorocarbon gas pulses and wherein pulsing said hydrofluorcarbon gas imparts a time varying flow rate to said hydrofluorcarbon gas for a plurality of periods of said time varying flow rate.

Sub C 15

35. (Twice Amended) An etching method comprising:
exposing a substrate to a plurality of gases, wherein at least one of said gases is
pulsed and said pulsing imparts a time varying flow rate to said at least one gas for a plurality
of periods of said time varying flow rate; and wherein
b3
at least one of said gases comprises an etchant gas selected from the group consisting
of a hydrofluorocarbon and a fluorocarbon; and
at least one of said gases comprises a polymer forming gas for depositing a protective
layer.

Sub C 19

41. (Once Amended) A method to control etch profile while etching a microelectronics
substrate, the method comprising:

b4
providing an etch chamber and a microelectronics substrate disposed therein;
pulsing into said etch chamber a carbon containing polymer gas suitable for:
forming a deposit on at least a portion of said microelectronics substrate; and
etching said microelectronics substrate;
wherein said pulsing imparts a time varying flow rate to said gas for a plurality of periods of
said time varying flow rate, thereby causing said gas to alternately form a deposit on at least a portion
of said microelectronics substrate and etch said microelectronics substrate.